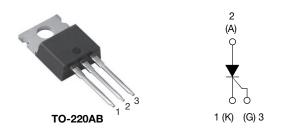
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Thyristor High Voltage, Phase Control SCR, 25 A



PRIMARY CHARACTERISTICS					
I _{T(AV)}	16 A				
V _{DRM} /V _{RRM}	1200 V				
V _{TM}	1.25 V				
I _{GT}	45 mA				
TJ	-40 °C to +125 °C				
Package	TO-220AB				
Circuit configuration	Single SCR				

FEATURES

- Easy control peak current at charger power up to reduce passive / electromechanical components
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power **FREE** rectification
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- On-board and off-board EV/HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-25TTS12HM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS			
Capacitive input filter $T_A = 55 \text{ °C}$, $T_J = 125 \text{ °C}$, common heatsink of 1 °C/W	18	22	А			

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	16	٨			
I _{RMS}		25	A			
V _{RRM} /V _{DRM}		1200	V			
I _{TSM}		320	А			
V _T	16 A, T _J = 25 °C	1.25	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
TJ		-40 to +125	°C			

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA
VS-25TTS12HM3	1200	1200	10



RoHS

COMPLIANT

VS-25TTS12HM3



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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CO	NDITIONS	VAL	UNITS		
FANAMETEN	STMBOL	TY		TYP.	MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	$T_{\rm C}$ = 93 °C, 180° conduc	tion half sine wave	1	6		
Maximum RMS on-state current	I _{RMS}			2	:5	А	
Maximum peak, one-cycle,		10 ms sine pulse, rated V	/ _{RRM} applied	2	70	~	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no vol	tage reapplied	33	20		
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V	√ _{RRM} applied	3	65	A ² s	
Maximum 1-t for fusing	1-1	10 ms sine pulse, no vol	tage reapplied	515		A-5	
Maximum I²√t for fusing	l²√t	t = 0.1 to 10 ms, no volta	age reapplied	51	52	A²√s	
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C	1.	25	V		
On-state slope resistance	r _t	T _ 105 °C		12	2.0	mΩ	
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1	.0	V	
Maximum reverse and direct leakage	I _{BM} /I _{DM}	T _J = 25 °C	V_{-} = rated $V_{}$	0	.5		
current	'RM/ 'DM	$T_J = 125 \degree C$ $V_R = rated V_{RRM}/V_{DRM}$		1	0		
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 $^\circ C$		-	150	mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$			00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 %, $V_{DRM} = R_g - k = open$			00	V/µs	
Maximum rate of rise of turned-on current	dl/dt			1:	50	A∕µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	w	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+I _{GM}		1.5	A	
Maximum peak negative gate voltage	-V _{GM}		10	V	
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	60	mA	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	45		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20		
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	2.5		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	oad, $T_{J} = 25 ^{\circ}C$ 2.0		
voltage to trigger		Anode supply = 6 V, resistive load, $T_J = 125 \degree C$	1.0	V	
Maximum DC gate voltage not to trigger	V _{GD}		0.25		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T ₁ = 125 °C	4	μs
Typical turn-off time	tq	1j = 125 C	110	

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VS-25TTS12HM3

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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storag	e	T _J , T _{Stg}		-40 to 125	°C		
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.1			
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W		
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5			
Approximate weight				2	g		
Approximate weight				0.07	oz.		
Mounting torque	minimum			6 (5)	kgf ⋅ cm		
Mounting torque	maximum			12 (10)	(lbf ⋅ in)		
Marking device			Case style TO-220AB	25TT	S12H		

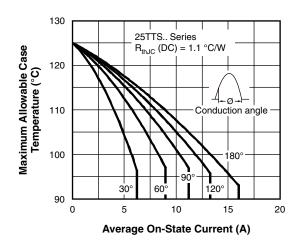


Fig. 1 - Current Rating Characteristics

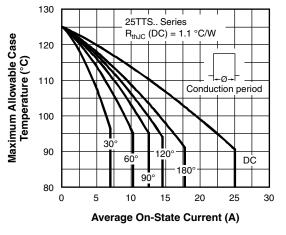


Fig. 2 - Current Rating Characteristics

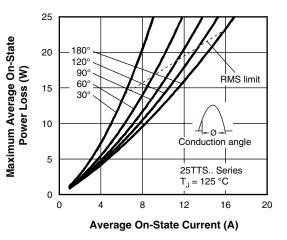


Fig. 3 - On-State Power Loss Characteristics

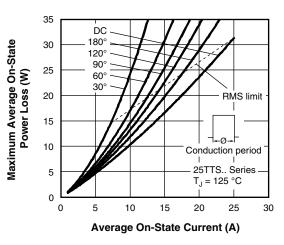


Fig. 4 - On-State Power Loss Characteristics

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VS-25TTS12HM3



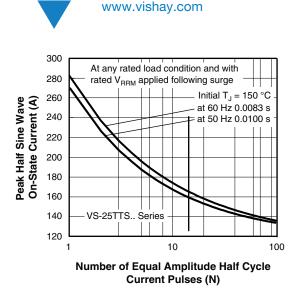
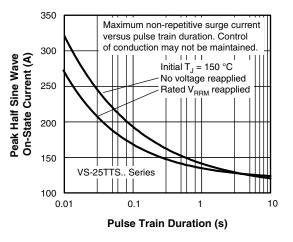


Fig. 5 - Maximum Non-Repetitive Surge Current





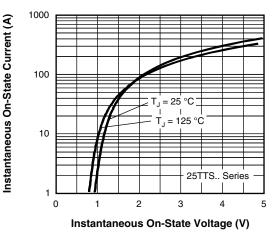


Fig. 7 - On-State Voltage Drop Characteristics

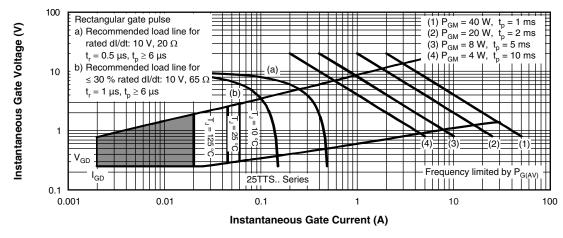


Fig. 8 - Gate Characteristics

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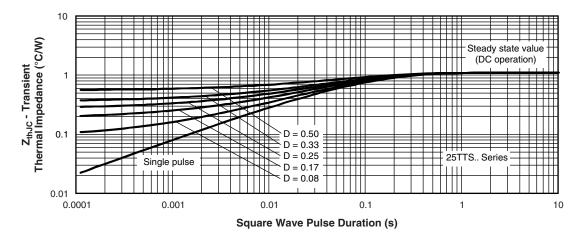
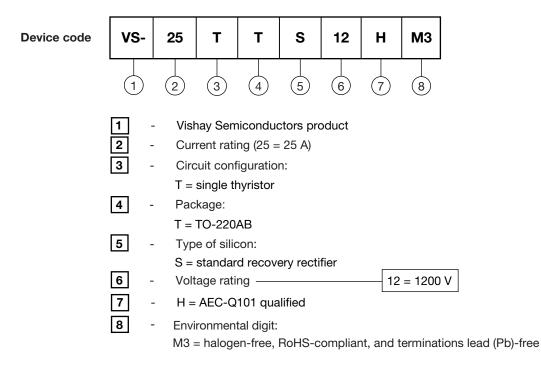


Fig. 9 - Thermal Impedance ZthJC Characteristics

ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-25TTS12HM3	50	1000	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95222			
Part marking information	www.vishay.com/doc?95028			

Revision: 26-Nov-2024 For technical questions within your region: Dio

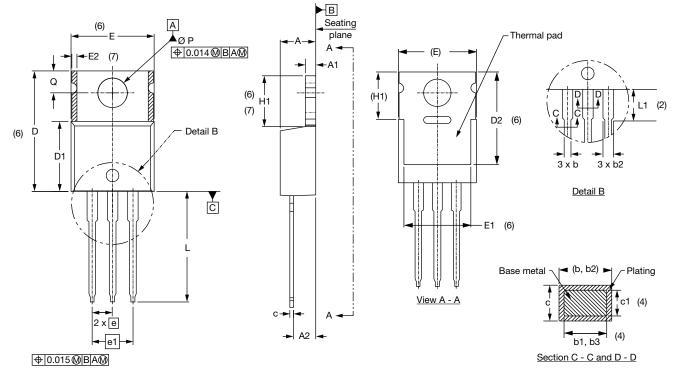
Outline Dimensions



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead tip

reten Teten reten

Conforms to JEDEC[®] outline TO-220AB

SYMBOL	MILLIN	MILLIMETERS INCHE		INCHES		TES SYMBOL	MILLIN	IETERS	INC	HES	NOTES	
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			D2	11.68	12.88	0.460	0.507	6
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.56	2.92	0.101	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			E2	-	0.76	-	0.030	7
b1	0.38	0.97	0.015	0.038	4		е	2.41	2.67	0.095	0.105	
b2	1.20	1.73	0.047	0.068			e1	4.88	5.28	0.192	0.208	
b3	1.14	1.73	0.045	0.068	4		H1	5.84	6.86	0.230	0.270	6, 7
С	0.36	0.61	0.014	0.024			L	13.52	14.02	0.532	0.552	
c1	0.36	0.56	0.014	0.022	4		L1	3.32	3.82	0.131	0.150	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only

⁽⁵⁾ Controlling dimensions: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1

- ⁽⁷⁾ Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC[®] TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

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